

HT70xxA-1 TinyPower[™] Voltage Detector

Features

- · Low power consumption
- · Low temperature coefficient
- High input voltage range (up to 24V)
- Output voltage accuracy: tolerance ± 3%
- · Built-in hysteresis characteristic
- TO92, SOT89, SOT23 and SOT23-5 package

Applications

- · Battery checkers
- · Level selectors
- · Power failure detectors

- Microcomputer reset
- · Battery memory backup
- · Non-volatile RAM signal storage protectors

General Description

The HT70xxA-1 series devices area set of three terminal low power voltage detectors implemented in CMOS technology. Each voltage detector in the series detects a particular fixed voltage ranging from 2.2V to 5V. The voltage detectors consist of a high-precision and low power consumption standard voltage source as well as a

comparator, hysteresis circuit, and an output driver. CMOS technology ensures low power consumption.

Although designed primarily as fixed voltage detectors, these devices can be used with external components to detect user specified threshold voltages.

Selection Table

Part No.	Detectable Voltage	Hysteresis Width	Tolerance	Package	Marking
HT7022A-1	2.2V	0.11V	±3%		
HT7024A-1	2.4V	0.12V	±3%		70xxA-1 (for TO92)
HT7027A-1	2.7V	0.135V	±3%	TO92	70xxA-1# (for SOT89)
HT7033A-1	3.3V	0.165V	±3%	SOT89 SOT23	70xxA-1+ (for SOT89) 0xxA+ (for SOT23)
HT7039A-1	3.9V	0.195V	±3%	SOT23-5	0xxA# (for SOT23-5)
HT7044A-1	4.4V	0.22V	±3%		0xxA+ (for SOT23-5)
HT7050A-1	5.0V	0.25V	±3%		

Note: "xx" stands for output voltages.

Both lead free and green compound devices are available. Note the symbol marks below:

For the TO92 package, the symbol mark will be at the end of the date code. Whereas for the SOT89, SOT23 and SOT23-5, the symbol mask will be located at the end of IC marking.

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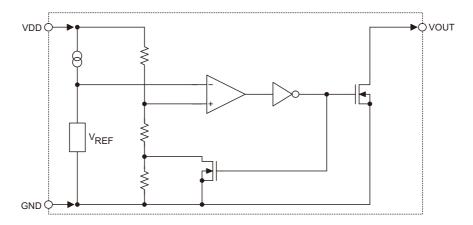
[&]quot;#" stands for lead free devices.

[&]quot;+" stands for green compound devices, which are Lead-free and Halogen-free.



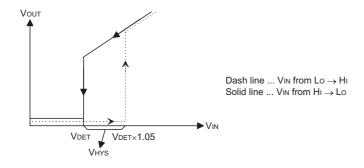
Block Diagram

N Channel Open Drain Output (Normal Open; Active Low)

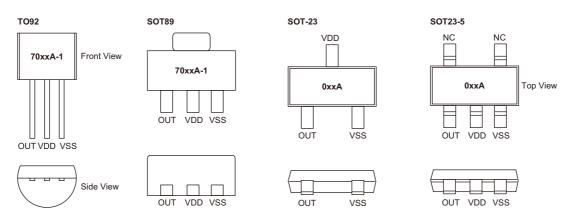


Output Table & Curve

V _{DD}	V _{DD} >V _{DET} (+)	V _{DD} ≤V _{DET} (−)
V _{OUT}	Hi-Z	VSS



Pin Assignment



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Absolute Maximum Ratings

Supply Voltage			V_{SS} -0.3V to V_{SS} +26V
Output Voltage	V_{SS} -0.3V to V_{DD} +0.3V	Output Current	50mA
Storage Temperature	50°C to 125°C	Power Consumption	200mW
Operating Temperature	40°C to 85°C		

Note: These are stress ratings only. Stresses exceeding the range specified under "Absolute Maximum Ratings" may cause substantial damage to the device. Functional operation of this device at other conditions beyond those listed in the specification is not implied and prolonged exposure to extreme conditions may affect device reliability.

Electrical Characteristics

HT7022A-1 Ta=25°C

Symbol	mbol Parameter Test Conditions V _{DD} Conditions		Test Conditions		Turn	Max.	Unit
Symbol			Conditions	Min.	Тур.	IVIAX.	Offic
V _{DET}	Detection Voltage	_		2.134	2.200	2.266	V
V _{HYS}	Hysteresis Width	_	_	0.02 V _{DET}	0.05 V _{DET}	0.1 V _{DET}	V
I _{DD}	Operating Current	3.2V	No load		3	6	μА
V_{DD}	Operating Voltage	_		1.5	_	24	V
I _{OL}	Output Sink Current	2V	V _{OUT} =0.2V	0.5	1	_	mA
$\frac{\Delta V_{\text{DET}}}{\Delta T_{a}}$	Temperature Coefficient	_	-40°C <ta<85°c< td=""><td>_</td><td>±1.1</td><td>_</td><td>mV/°C</td></ta<85°c<>	_	±1.1	_	mV/°C

HT7024A-1 Ta=25°C

Symbol	Parameter	Те	Test Conditions		Turn	Max.	Unit
Symbol	Parameter	V _{DD} Conditions		Min.	Тур.	IVIAX.	Onit
V _{DET}	Detection Voltage	_		2.328	2.400	2.472	V
V _{HYS}	Hysteresis Width		·	0.02 V _{DET}	0.05 V _{DET}	0.1 V _{DET}	V
I _{DD}	Operating Current	3.4V	No load		3	6	μА
V_{DD}	Operating Voltage	_	_	1.5	_	24	V
I _{OL}	Output Sink Current	2V	V _{OUT} =0.2V	0.5	1	_	mA
$\frac{\Delta V_{\text{DET}}}{\Delta T_{a}}$	Temperature Coefficient	_	-40°C <ta<85°c< td=""><td>_</td><td>±0.9</td><td>_</td><td>mV/°C</td></ta<85°c<>	_	±0.9	_	mV/°C

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HT7027A-1 Ta=25°C

Cumbal	Parameter Test Conditions		Min.	Trees	Max.	Unit	
Symbol	Parameter	V _{DD}	Conditions	IVIIII.	Тур.	iviax.	Unit
V _{DET}	Detection Voltage	_	_	2.619	2.700	2.781	V
V _{HYS}	Hysteresis Width	_	_	0.02 V _{DET}	0.05 V _{DET}	0.1 V _{DET}	V
I _{DD}	Operating Current	3.7V	No load		3	6	μА
V_{DD}	Operating Voltage	_	_	1.5	_	24	V
I _{OL}	Output Sink Current	2V	V _{OUT} =0.2V	0.5	1	_	mA
$\frac{\Delta V_{DET}}{\Delta T_{a}}$	Temperature Coefficient	_	-40°C <ta<85°c< td=""><td>_</td><td>±0.9</td><td>_</td><td>mV/°C</td></ta<85°c<>	_	±0.9	_	mV/°C

HT7033A-1 Ta=25°C

Cumbal	Parameter Test Conditions V _{DD} Conditions		Test Conditions		Trees	May	Unit
Symbol			Min.	Тур.	Max.	Unit	
V _{DET}	Detection Voltage	_		3.201	3.300	3.399	V
V _{HYS}	Hysteresis Width		_	0.02 V _{DET}	0.05 V _{DET}	0.1 V _{DET}	V
I _{DD}	Operating Current	4.3V	No load		3	6	μА
V _{DD}	Operating Voltage	_	_	1.5		24	V
I _{OL}	Output Sink Current	2.5V	V _{OUT} =0.25V	1.2	2.5		mA
$\frac{\Delta V_{DET}}{\Delta T_{a}}$	Temperature Coefficient	_	-40°C <ta<85°c< td=""><td>_</td><td>±0.9</td><td>_</td><td>mV/°C</td></ta<85°c<>	_	±0.9	_	mV/°C

HT7039A-1 Ta=25°C

Symbol			st Conditions	Min.	Turn	Max.	Unit
Symbol	Parameter	V _{DD}	Conditions	IVIIII.	Тур.	wax.	Unit
V _{DET}	Detection Voltage	_	_	3.783	3.900	4.017	V
V _{HYS}	Hysteresis Width	_	_	0.02 V _{DET}	0.05 V _{DET}	0.1 V _{DET}	V
I _{DD}	Operating Current	4.9V	No load		3	6	μА
V_{DD}	Operating Voltage	_		1.5		24	V
I _{OL}	Output Sink Current	2.5V	V _{OUT} =0.25V	1.2	2.5		mA
$\frac{\Delta V_{DET}}{\Delta T_{a}}$	Temperature Coefficient	_	-40°C <ta<85°c< td=""><td>_</td><td>±0.9</td><td>_</td><td>mV/°C</td></ta<85°c<>	_	±0.9	_	mV/°C



Symbol	Parameter Test Cond		st Conditions	Min.	Turn	Max.	Unit
Syllibol	Farameter	V _{DD} Conditions		IVIIII.	Тур.	IVIAX.	Offic
V _{DET}	Detection Voltage	_	_	4.268	4.400	4.532	V
V _{HYS}	Hysteresis Width			0.02	0.05	0.1	V
-1113	Tryotoreolo vvidar			V _{DET}	V _{DET}	V _{DET}	•
I _{DD}	Operating Current	5.4V	No load	_	3	6	μΑ
V_{DD}	Operating Voltage	_	_	1.5	_	24	V
I _{OL}	Output Sink Current	3.6V	V _{OUT} =0.36V	3	6	_	mA
$\frac{\Delta V_{DET}}{\Delta T_{a}}$	Temperature Coefficient	_	-40°C <ta<85°c< td=""><td>_</td><td>±0.9</td><td>_</td><td>mV/°C</td></ta<85°c<>	_	±0.9	_	mV/°C

HT7050A-1

Symbol	Parameter	Test Conditions		Min.	Tim	Max.	Unit
Symbol	Farameter	V _{DD}	Conditions	IVIIII.	Тур.	IVIAX.	Onit
V _{DET}	Detection Voltage	_	_	4.850	5.000	5.150	V
V _{HYS}	Hysteresis Width	_	_	0.02 V _{DET}	0.05 V _{DET}	0.1 V _{DET}	V
I _{DD}	Operating Current	6.0V	No load	_	3	6	μА
V_{DD}	Operating Voltage	_	_	2.1		24	V
I _{OL}	Output Sink Current	3.6V	V _{OUT} =0.36V	3	6	_	mA
$\frac{\Delta V_{DET}}{\Delta T_{a}}$	Temperature Coefficient	_	-40°C <ta<85°c< td=""><td>_</td><td>±0.9</td><td>_</td><td>mV/°C</td></ta<85°c<>	_	±0.9	_	mV/°C

Functional Description

The HT70xxA-1 series is a set of voltage detectors equipped with a high stability voltage reference which is connected to the negative input of a comparator—denoted as V_{REF} in the following figure for NMOS output voltage detector.

When the voltage drop to the positive input of the comparator (i,e,V_B) is higher than $V_{REF},\ VOUT$ goes high, M1 turns off, and V_B is expressed as $V_{BH} = V_{DD} \times (R_B + R_C) \ / \ (R_A + R_B + R_C).$ If V_{DD} is decreased so that V_B falls to a value less than $V_{REF},$ the comparator output inverts from high to low, V_{OUT} goes low, V_C is high, M1 turns on, RC is bypassed, and V_B becomes: $V_{BL} = V_{DD} \times R_B \ / \ (R_A + R_B),$ which is less than $V_{BH}.$ By so doing, the comparator output will stay low to prevent the circuit from oscillating when $V_B \approx V_{REF}.$

If V_{DD} falls below the minimum operating voltage, the output becomes undefined. When VDD goes from low to $V_{DD} \times R_B / (R_A + R_B) > V_{REF}$, the comparator output and V_{OUT} goes high.

The detectable voltage is defined as:

$$V_{DET}(-) = \frac{R_A + R_B + R_C}{R_B + R_C} \times V_{REF}$$

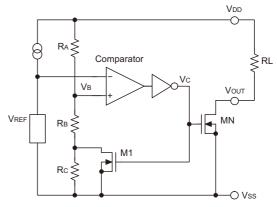
The release voltage is defined as:

$$V_{DET}\left(+ \right) = \frac{R_{A} + R_{B}}{R_{B}} \times V_{REF}$$

The hysteresis width is:

$$V_{HYS} = V_{DET}(+) - V_{DET}(-)$$

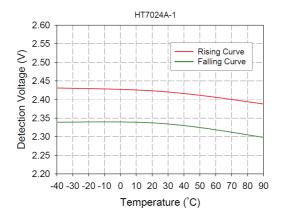
The figure demonstrates the NMOS output type with positive output polarity (V_{OUT} is normally open, active low). The HT70xxA-1 series also supplies options for other output types with active high outputs. Application circuits shown are examples of positive output polarity (normally open, active low) unless otherwise specified.

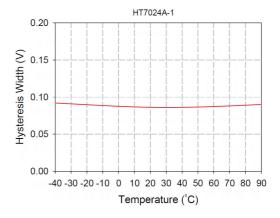


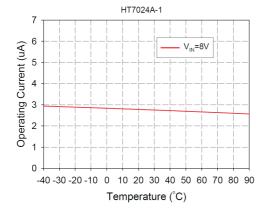
NMOS Output Voltage Detector

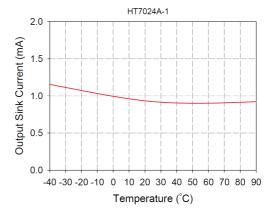


Typical Performance Characteristics









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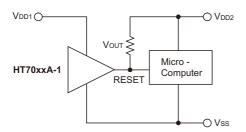


Application Circuits

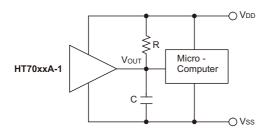
Microcomputer Reset Circuit

Normally a reset circuit is required to protect the microcomputer system from malfunctions due to power line interruptions. The following examples show how different output configurations perform a reset function in various systems.

NMOS open drain output application for separate power supply

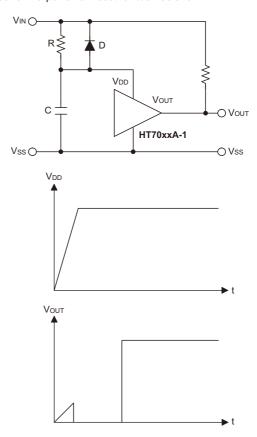


• NMOS open drain output application with R-C delay



Power-on Reset Circuit

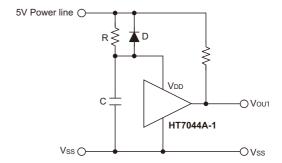
With several external components, the NMOS open drain type of the HT70xxA-1 series can be used to perform a power-on reset function as shown:



5V Power Line Monitoring Circuit

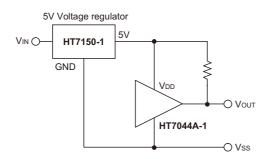
Generally, a minimum operating voltage of 4.5V is guaranteed in a 5V power line system. The HT7044A-1 is recommended for use as 5V power line monitoring circuit

• 5V power line monitor with power-on reset





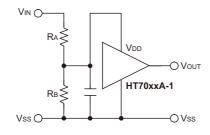
• with 5V voltage regulator



Change of Detectable Voltage

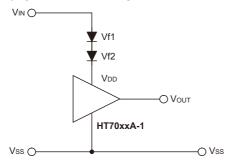
If the required voltage is not found in the standard product selection table, it is possible to change it by using external resistance dividers or diodes.

Varying the detectable voltage with a resistance divider



$$\begin{aligned} & \text{Detectable voltage} = \frac{R_{\text{A}} + R_{\text{B}}}{R_{\text{B}}} \times V_{\text{DET}} \\ & \text{Hysteresis width} = \frac{R_{\text{A}} + R_{\text{B}}}{R_{\text{B}}} \times V_{\text{HYS}} \end{aligned}$$

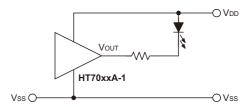
• Varying the detectable voltage with a diode



Detectable Voltage = $V_{f1}+V_{f2}+V_{DET}$

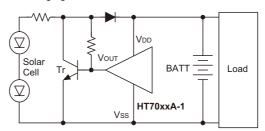
Malfunction Analysis

The following circuit demonstrates the way a circuit analyzes malfunctions by monitoring the variation or spike noise of power supply voltage.



Charge Monitoring Circuit

The following circuit shows a charged monitor for protection against battery deterioration by overcharging. When the voltage of the battery is higher than the set detectable voltage, the transistor turns on to bypass the charge current, protecting the battery from overcharging.

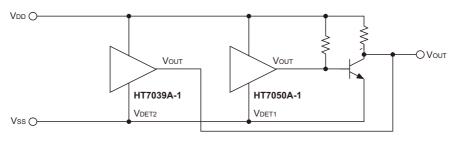


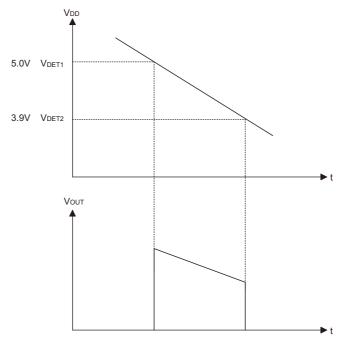
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Level Selector

The following diagram illustrates a logic level selector.





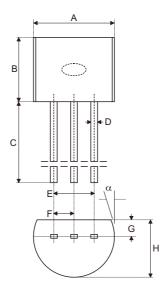
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Package Information

Note that the package information provided here is for consultation purposes only. As this information may be updated at regular intervals users are reminded to consult the Holtek website (http://www.holtek.com.tw/english/literature/package.pdf) for the latest version of the package information.

3-pin TO92 Outline Dimensions



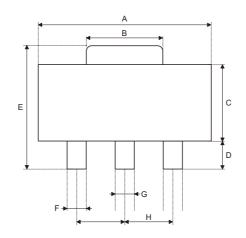
Symbol	Dimensions in inch						
Зупроі	Min.	Nom.	Max.				
Α	0.170	_	0.200				
В	0.170	_	0.200				
С	0.500	_	_				
D	0.011	_	0.020				
E	0.090	_	0.110				
F	0.045	_	0.055				
G	0.045	_	0.065				
Н	0.130	_	0.160				
α	0°	_	10°				

Symbol	Dimensions in mm		
Symbol	Min.	Nom.	Max.
A	4.32	_	5.08
В	4.32	_	5.08
С	12.70	_	_
D	0.28	_	0.51
E	2.29	_	2.79
F	1.14	_	1.40
G	1.14	_	1.65
Н	3.30	_	4.06
α	0°	_	10°

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3-pin SOT89 Outline Dimensions





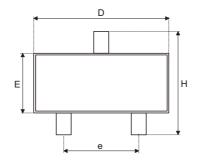
Cumbal	Dimensions in inch		
Symbol	Min.	Nom.	Max.
Α	0.173	_	0.181
В	0.059	_	0.072
С	0.090	_	0.102
D	0.035	_	0.047
E	0.155	_	0.167
F	0.014	_	0.019
G	0.017	_	0.022
Н	_	0.059	_
I	55	_	63
J	14	_	17

Cumbal	Dimensions in mm		
Symbol	Min.	Nom.	Max.
A	4.39	_	4.60
В	1.50	_	1.83
С	2.29	_	2.59
D	0.89	_	1.19
Е	3.94	_	4.24
F	0.36	_	0.48
G	0.43	_	0.56
Н	_	1.50	_
I	1.40	_	1.60
J	0.36	_	0.43

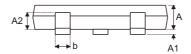
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3-pin SOT23 Outline Dimensions







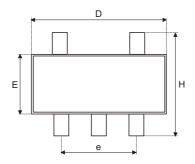
Symbol	Dimensions in inch		
Symbol	Min.	Nom.	Max.
Α	0.039	_	0.051
A1	_		0.004
A2	0.028	_	0.035
b	0.014	_	0.020
С	0.004	_	0.010
D	0.106	_	0.122
E	0.055	_	0.071
е	_	0.075	_
Н	0.102	_	0.118
L	0.015	_	_
θ	0°	_	9°

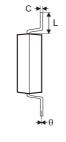
Cumhal	Dimensions in mm		
Symbol	Min.	Nom.	Max.
Α	1.00	_	1.30
A1	_	_	0.10
A2	0.70	_	0.90
b	0.35	_	0.50
С	0.10	_	0.25
D	2.70	_	3.10
E	1.40	_	1.80
е	_	1.90	_
Н	2.60	_	3.00
L	0.37	_	_
θ	0°	_	9°

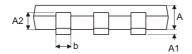
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5-pin SOT23-5 Outline Dimensions







Symbol	Dimensions in inch		
Symbol	Min.	Nom.	Max.
A	0.039	_	0.051
A1	_	_	0.004
A2	0.028	_	0.035
b	0.014	_	0.020
С	0.004	_	0.010
D	0.106	_	0.122
E	0.055	_	0.071
е	_	0.075	_
Н	0.102	_	0.118
L	0.015	_	_
θ	0°	_	9°

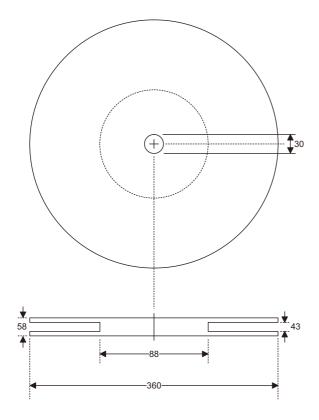
Cumhal	Dimensions in mm		
Symbol	Min.	Nom.	Max.
Α	1.00	_	1.30
A1	_	_	0.10
A2	0.70	_	0.90
b	0.35	_	0.50
С	0.10	_	0.25
D	2.70	_	3.10
E	1.40	_	1.80
е	_	1.90	_
Н	2.60	_	3.0
L	0.37	_	_
θ	0°	_	9°

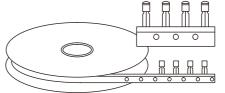
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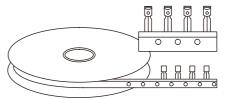
Product Tape and Reel Specifications

TO92 Reel Dimensions (Unit: mm)





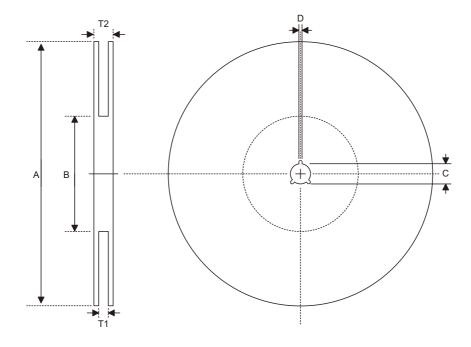
Package Up, Flat Side Up



Package Up, Flat Side Down



Reel Dimensions



SOT89-3

Symbol	Description	Dimensions in mm
Α	Reel Outer Diameter	180.0±1.0
В	Reel Inner Diameter	62.0±1.5
С	Spindle Hole Diameter	12.75 +0.15/-0.00
D	Key Slit Width	1.90±0.15
T1	Space Between Flange	12.4 +0.2/-0.0
T2	Reel Thickness	17.0 +0.0/-0.4

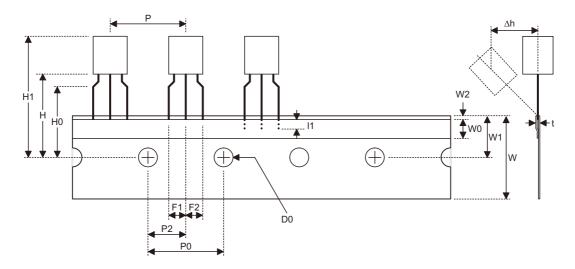
SOT23-3, SOT23-5

Symbol	Description	Dimensions in mm
Α	Reel Outer Diameter	178.0±1.0
В	Reel Inner Diameter	62.0±1.0
С	Spindle Hole Diameter	13.0±0.2
D	Key Slit Width	2.50±0.25
T1	Space Between Flange	8.4 +1.5/-0.0
T2	Reel Thickness	11.4 +1.5/-0.0

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Carrier Tape Dimensions



TO92

Symbol	Description	Dimensions in mm
I1	Taped Lead Length	(2.5)
Р	Component Pitch	12.7±1.0
P ₀	Perforation Pitch	12.7±0.3
P ₂	Component to Perforation (Length Direction)	6.35±0.40
F ₁	Lead Spread	2.5 +0.4/-0.1
F ₂	Lead Spread	2.5 +0.4/-0.1
Δh	Component Alignment	0.0±0.1
W	Carrier Tape Width	18.0 +1.0/-0.5
W ₀	Hold-down Tape Width	6.0±0.5
W ₁	Perforation Position	9.0±0.5
W ₂	Hold-down Tape Position	(0.5)
H ₀	Lead Clinch Height	16.0±0.5
H ₁	Component Height	Less than 24.7
D ₀	Perforation Diameter	4.0±0.2
t	Taped Lead Thickness	0.7±0.2
Н	Component Base Height	19.0±0.5

Note: Thickness less than 0.38 ± 0.05 mm~0.5mm

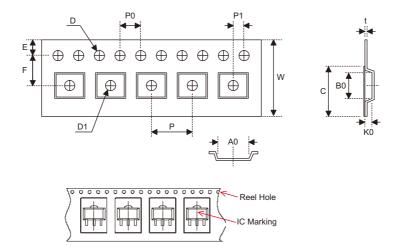
P0 Accumulated pitch tolerance: ± 1 mm/20pitches.

() Bracketed figures are for consultation only

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Carrier Tape Dimensions



SOT89-3

Symbol	Description	Dimensions in mm
W	Carrier Tape Width	12.0 +0.3/-0.1
Р	Cavity Pitch	8.0±0.1
Е	Perforation Position	1.75±0.10
F	Cavity to Perforation (Width Direction)	5.50±0.05
D	Perforation Diameter	1.5 +0.1/-0.0
D1	Cavity Hole Diameter	1.5 +0.1/-0.0
P0	Perforation Pitch	4.0±0.1
P1	Cavity to Perforation (Length Direction)	2.0±0.1
A0	Cavity Length	4.8±0.1
В0	Cavity Width	4.5±0.1
K0	Cavity Depth	1.8±0.1
t	Carrier Tape Thickness	0.300±0.013
С	Cover Tape Width	9.3±0.1

SOT23-3

Symbol	Description	Dimensions in mm
W	Carrier Tape Width	8.0±0.3
Р	Cavity Pitch	4.0±0.1
Е	Perforation Position	1.75±0.10
F	Cavity to Perforation (Width Direction)	3.50±0.05
D	Perforation Diameter	1.5 +0.1/-0.0
D1	Cavity Hole Diameter	1.5 +0.1/-0.0
P0	Perforation Pitch	4.0±0.1
P1	Cavity to Perforation (Length Direction)	2.00±0.05
A0	Cavity Length	3.15±0.10
В0	Cavity Width	3.2±0.1
K0	Cavity Depth	1.4±0.1
t	Carrier Tape Thickness	0.20±0.03
С	Cover Tape Width	5.3±0.1

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SOT23-5

Symbol	Description	Dimensions in mm
W	Carrier Tape Width	8.0±0.3
Р	Cavity Pitch	4.0±0.1
E	Perforation Position	1.75±0.10
F	Cavity to Perforation (Width Direction)	3.50±0.05
D	Perforation Diameter	1.5 +0.1/-0.0
D1	Cavity Hole Diameter	1.5 +0.1/-0.0
P0	Perforation Pitch	4.0±0.1
P1	Cavity to Perforation (Length Direction)	2.00±0.05
A0	Cavity Length	3.15±0.10
В0	Cavity Width	3.2±0.1
K0	Cavity Depth	1.4±0.1
t	Carrier Tape Thickness	0.20±0.03
С	Cover Tape Width	5.3±0.1



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